

## Turbo 2 ultrafast high voltage rectifier

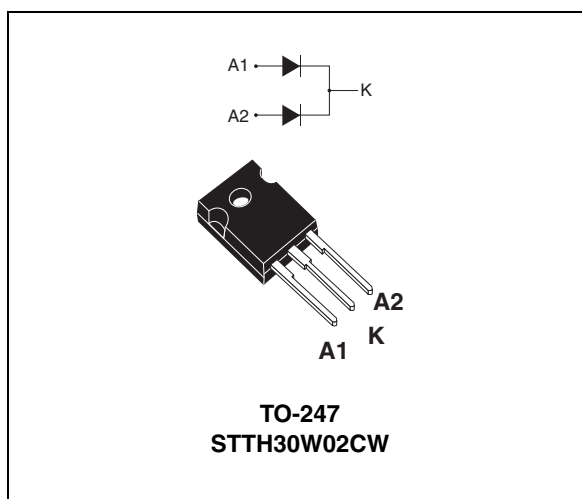
Datasheet – production data

### Features

- Ultrafast switching
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses
- ECOPACK<sup>®</sup>2 compliant component

### Description

The STTH30W02CW, uses ST Turbo 2, 200 V technology. It is especially suited to be used for DC/DC and DC/AC converters in secondary stage of MIG/MMA/TIG welding machine. Housed in ST's TO-247, this device offers high power integration for all welding machines and industrial applications.



**Table 1. Device summary**

Symbol	Value
$I_{F(AV)}$	2 x 15 A
$V_{RRM}$	200 V
$t_{rr}$ (typ)	20 ns
$T_j$ (max)	175 °C
$V_F$ (typ)	0.90 V

# 1 Characteristics

**Table 2. Absolute ratings (limiting values, at 25 °C, unless otherwise specified)**

Symbol	Parameter		Value	Unit	
V <sub>RRM</sub>	Repetitive peak reverse voltage		200	V	
I <sub>F(RMS)</sub>	Forward rms current		30	A	
I <sub>F(AV)</sub>	Average forward current, δ = 0.5	T <sub>c</sub> = 125 °C	Per diode	15	A
		T <sub>c</sub> = 115 °C	Per device	30	
I <sub>FSM</sub>	Surge non repetitive forward current	t <sub>p</sub> = 10 ms sinusoidal	140	A	
T <sub>stg</sub>	Storage temperature range		-65 to + 175	°C	
T <sub>j</sub>	Maximum operating junction temperature		+ 175	°C	

**Table 3. Thermal resistance**

Symbol	Parameter		Value	Unit
R <sub>th(j-c)</sub>	Junction to case	Per diode	2.5	°C / W
		Total	1.5	
R <sub>th(c)</sub>	Coupling		0.5	

When diodes 1 and 2 are used simultaneously:

$$T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

**Table 4. Static electrical characteristics**

Symbol	Parameter	Test conditions		Min.	Typ	Max.	Unit
I <sub>R</sub> <sup>(1)</sup>	Reverse leakage current	T <sub>j</sub> = 25 °C	V <sub>R</sub> = V <sub>RRM</sub>			10	μA
		T <sub>j</sub> = 125 °C			5	50	
V <sub>F</sub> <sup>(2)</sup>	Forward voltage drop	T <sub>j</sub> = 25 °C	I <sub>F</sub> = 15A			1.20	V
		T <sub>j</sub> = 150 °C			0.90	1.05	
		T <sub>j</sub> = 25 °C	I <sub>F</sub> = 30 A			1.4	
		T <sub>j</sub> = 150 °C			1.1	1.3	

1. Pulse test: t<sub>p</sub> = 5 ms, δ < 2%

2. Pulse test: t<sub>p</sub> = 380 μs, δ < 2%

To evaluate the conduction losses use the following equation:

$$P = 0.8 \times I_{F(AV)} + 0.0167 I_{F(RMS)}^2$$

Table 5. Dynamic electrical characteristics

Symbol	Parameter	Test conditions		Min.	Typ	Max.	Unit
$I_{RM}$	Reverse recovery current	$T_j = 125\text{ }^\circ\text{C}$	$I_F = 15\text{ A}, V_R = 160\text{ V}$ $di_F/dt = -200\text{ A}/\mu\text{s}$		7	9	A
$Q_{RR}$	Reverse recovery charge				160		nC
$S_{factor}$	Softness factor				0.3		
$t_{rr}$	Reverse recovery time	$T_j = 25\text{ }^\circ\text{C}$	$I_F = 1\text{ A}, V_R = 30\text{ V}$ $di_F/dt = -100\text{ A}/\mu\text{s}$		20	25	ns
$t_{fr}$	Forward recovery time	$T_j = 25\text{ }^\circ\text{C}$	$I_F = 15\text{ A}, V_{FR} = 1.1\text{ V}$ $di_F/dt = 100\text{ A}/\mu\text{s}$			200	ns
$V_{FP}$	Forward recovery voltage	$T_j = 25\text{ }^\circ\text{C}$			1.6	2.4	V

Figure 1. Average forward power dissipation versus average forward current (per diode)

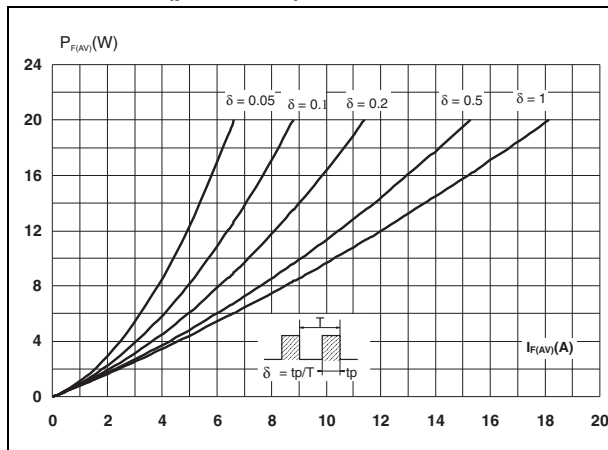


Figure 2. Forward voltage drop versus forward current (per diode)

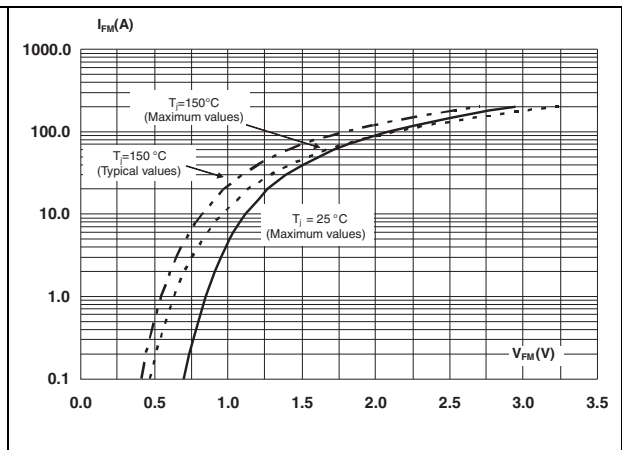


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

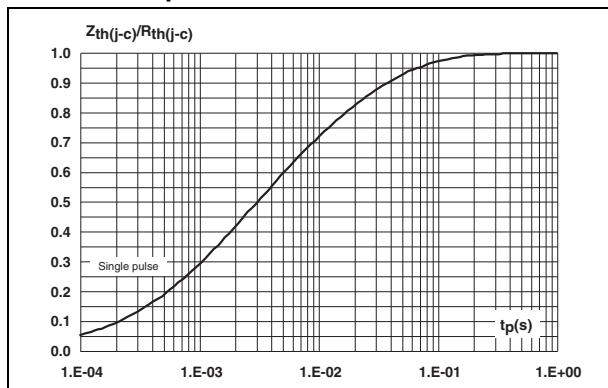


Figure 4. Peak reverse recovery current I\_RM (A) versus di\_F/dt (typical values, per diode)

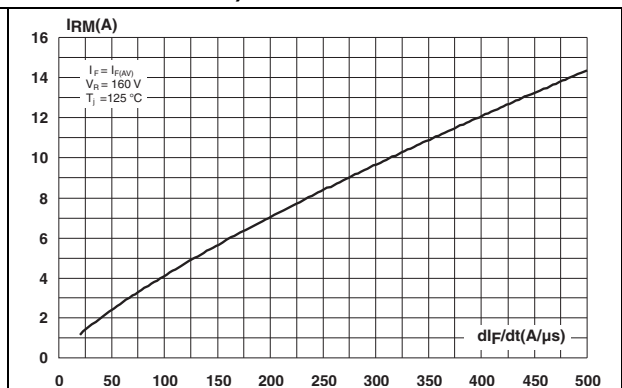


Figure 5. Reverse recovery time versus  $di_F/dt$  (typical values, per diode)

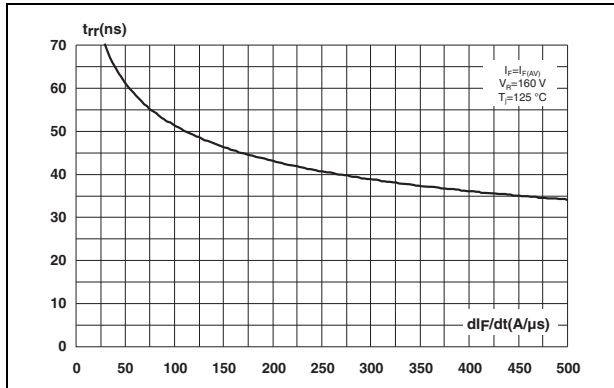


Figure 6. Reverse recovery charges versus  $di_F/dt$  (typical values, per diode)

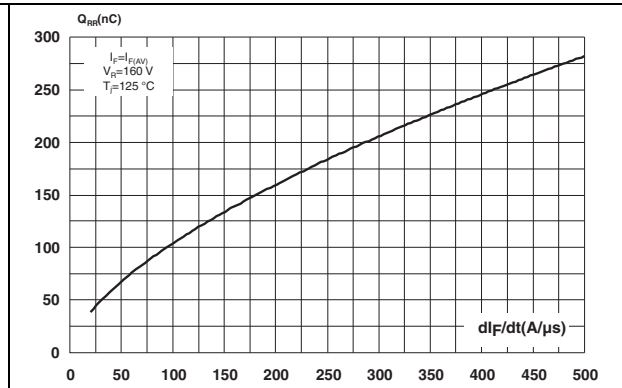


Figure 7. Relative variations of dynamic parameters versus junction temperature

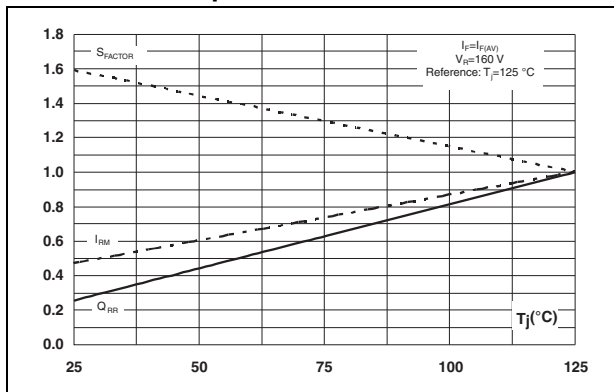


Figure 8. Reverse recovery softness factor versus  $di_F/dt$  (typical values, per diode)

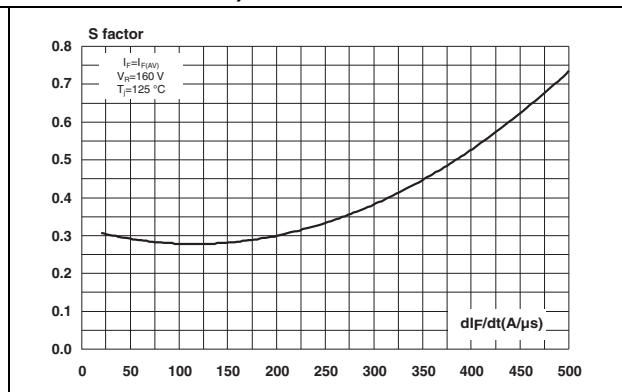


Figure 9. Forward recovery time versus  $di_F/dt$  (typical values, per diode)

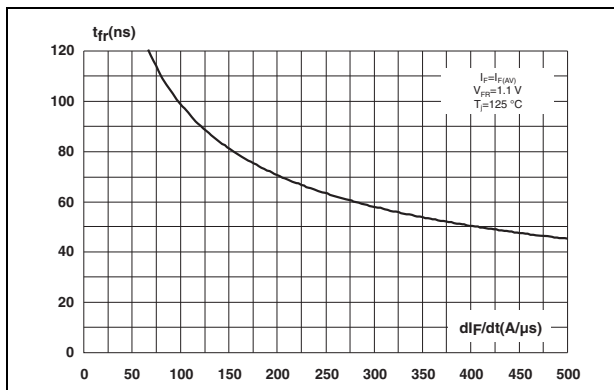


Figure 10. Transient peak forward voltage versus  $di_F/dt$  (typical values, per diode)

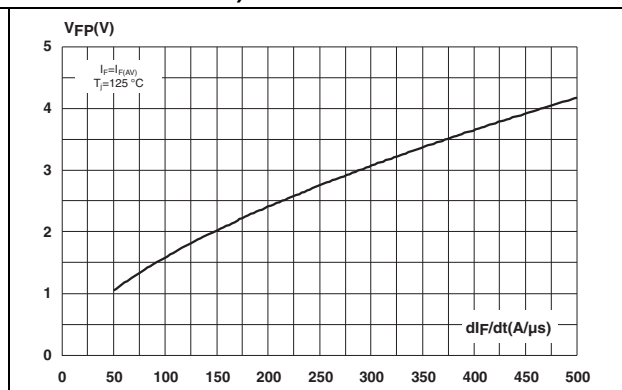
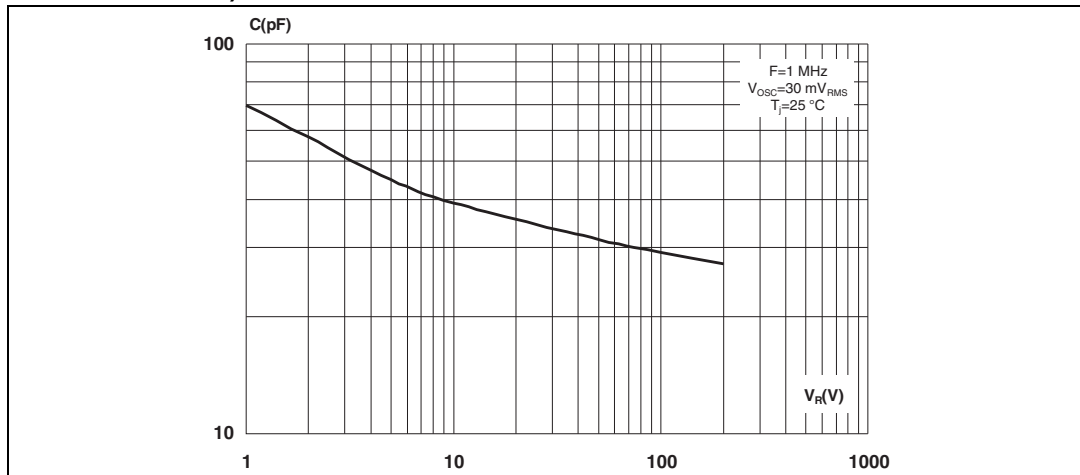


Figure 11. Junction capacitance versus reverse voltage applied (typical values, per diode)



## 2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.55 N·m (1.0 N·m maximum)

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**Table 6. TO-247 dimensions**

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.85		5.15	0.191		0.203
A1	2.20		2.60	0.086		0.102
b	1.00		1.40	0.039		0.055
b1	2.00		2.40	0.078		0.094
b2	3.00		3.40	0.118		0.133
c	0.40		0.80	0.015		0.031
D <sup>(1)</sup>	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e	5.30	5.45	5.60	0.209	0.215	0.220
L	14.20		14.80	0.559		0.582
L1	3.70		4.30	0.145		0.169
L2	18.50 typ.			0.728 typ.		
∅P <sup>(2)</sup>	3.55		3.65	0.139		0.143
∅R	4.50		5.50	0.177		0.217
S	5.30	5.50	5.70	0.209	0.216	0.224

1. Dimension D plus gate protrusion does not exceed 20.5 mm
2. Resin thickness around the mounting hole is not less than 0.9 mm

### 3 Ordering information

Table 7. Ordering information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STTH30W02CW	STTH30W02CW	TO-247	4.46 g	50	Tube

### 4 Revision history

Table 8. Document revision history

Date	Revision	Changes
05-Oct-2012	1	First issue.

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